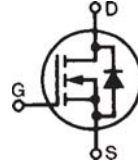


Linear Power MOSFET IXTB62N50L

With Extended FBSOA

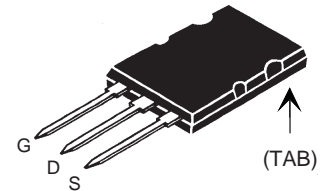
N-Channel Enhancement Mode



$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 62 \text{ A} \\ R_{DS(on)} &\leq 0.1 \text{ } \Omega \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	62	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	150	A
I_{AR}	$T_C = 25^\circ\text{C}$	62	A
E_{AR}	$T_C = 25^\circ\text{C}$	80	mJ
E_{AS}		5.0	J
P_D	$T_C = 25^\circ\text{C}$	800	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
F_c	Mounting force	20...120/4.5...27	N/lb.
Weight		10	g

PLUS 264™ (IXTB)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Designed for linear operation
- International standard package
- Unclamped Inductive switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Programmable loads
- Current regulators
- DC-DC converters
- Battery chargers
- DC choppers
- Temperature and lighting controls

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ } \mu\text{A}$	3		V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			50 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 20 \text{ V}$, $I_D = 0.5 I_{D25}$ Note 1			0.10 Ω

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		Min.	Typ.	Max.	
g _{fs}	V _{DS} = 10 V; I _D = 0.5 • I _{D25} , Note 1	10	15	20	S
C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	11500		pF	
C _{oss}		1460		pF	
C _{rss}		210		pF	
t _{d(on)}	V _{GS} = 15 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 2 Ω (External),	36		ns	
t _r		85		ns	
t _{d(off)}		110		ns	
t _f		75		ns	
Q _{g(on)}	V _{GS} = 20 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}	550		nC	
Q _{gs}		115		nC	
Q _{gd}		180		nC	
R _{thJC}				0.156 °C/W	
R _{thCS}		0.15		°C/W	

Safe Operating Area Specification

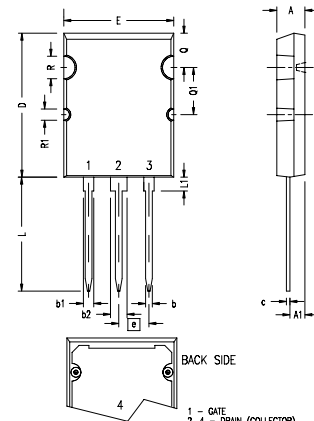
Symbol	Test Conditions	Min.	Typ.	Max.
SOA	V _{DS} = 400 V, I _D = 0.75 A, T _C = 90°C	300		W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
I _S	V _{GS} = 0 V			62 A
I _{SM}	Repetitive; pulse width limited by T _{JM}			176 A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5 V
t _{rr}	I _F = I _S , -di/dt = 100 A/μs, V _R = 100V		500	ns

Note 1: Pulse test, t ≤ 300 μs, duty cycle, d ≤ 2 %

PLUS 264™ (IXTB) Outline



NOTE: This drawing meets all dimensions requirement of JEDEC outlines TO-264 AA except screw hole area dimensions.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

Ref: IXYS CO 0113 R0

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

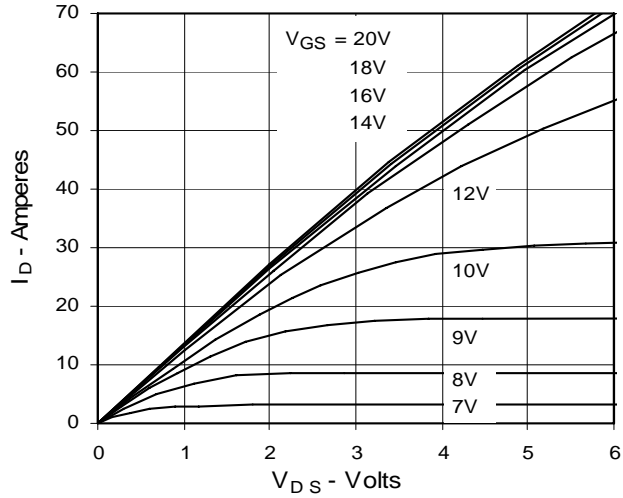


Fig. 2. Extended Output Characteristics @ 25°C

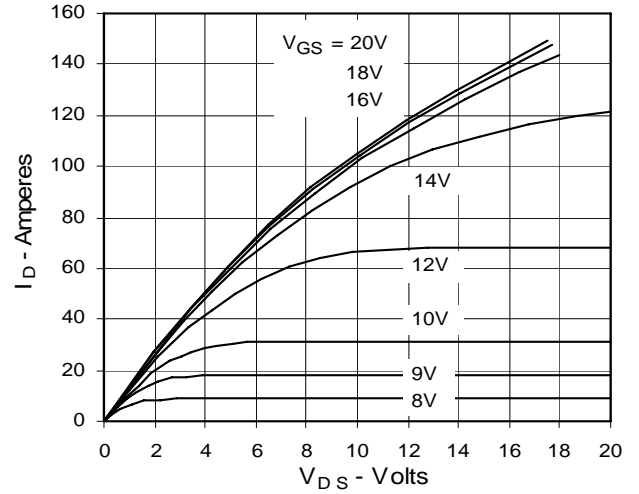


Fig. 3. Output Characteristics @ 125°C

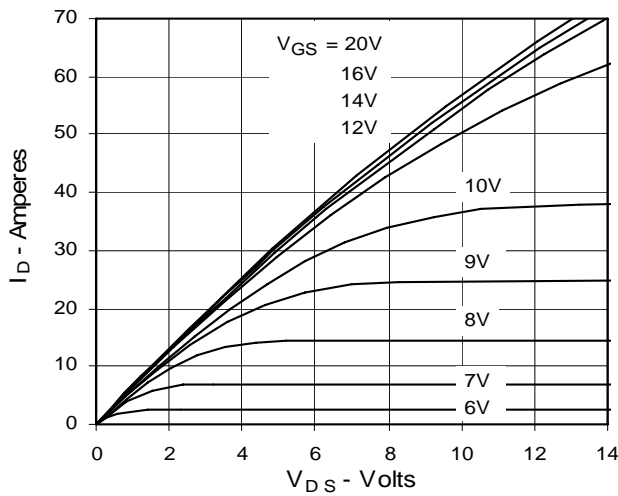


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

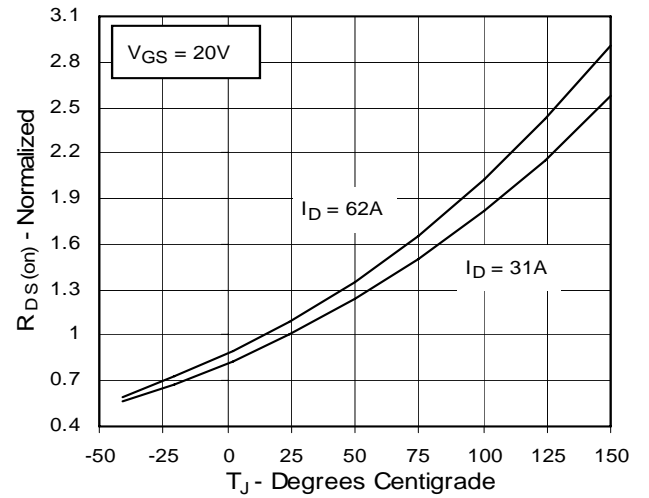


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

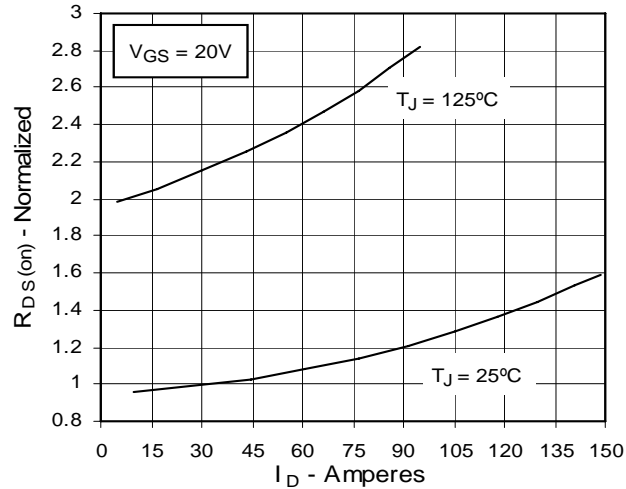


Fig. 6. Drain Current vs. Case Temperature

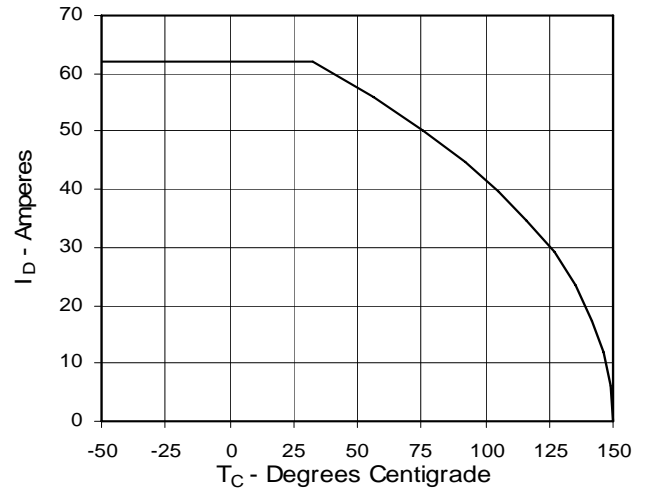


Fig. 7. Input Admittance

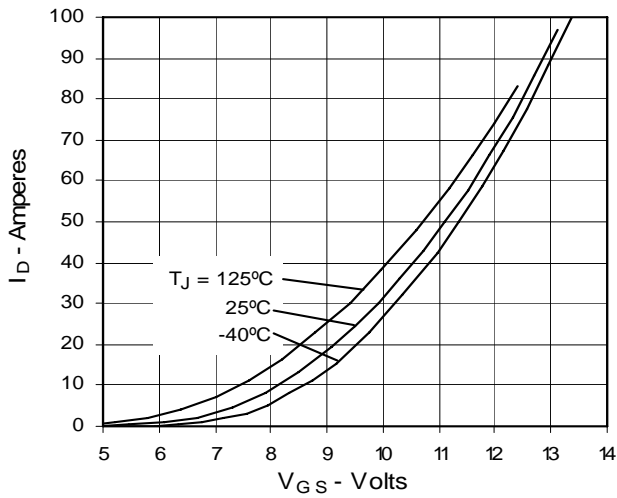


Fig. 8. Transconductance

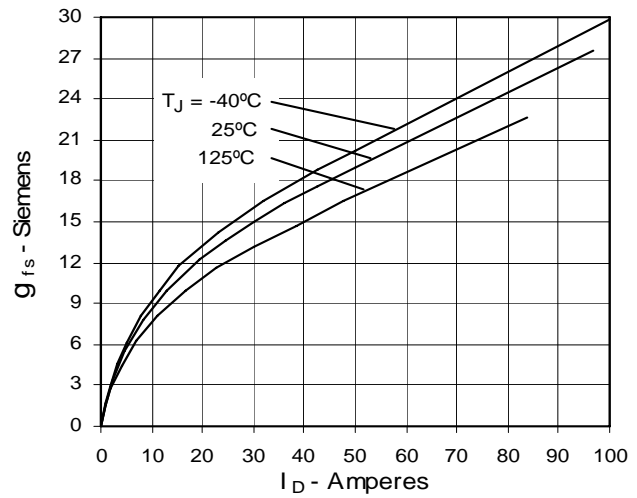


Fig. 9. Source Current vs. Source-To-Drain Voltage

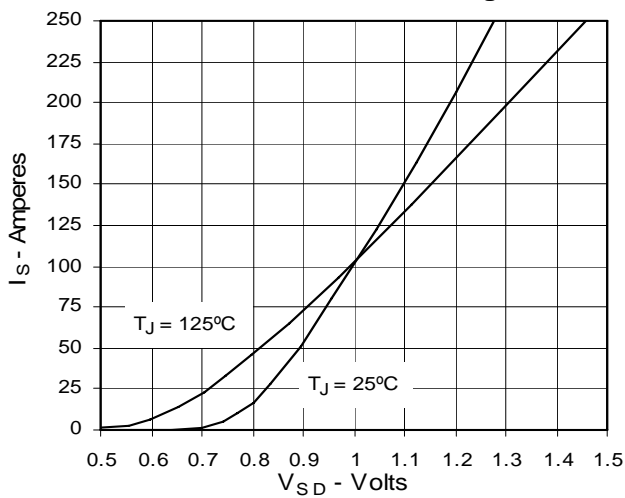


Fig. 10. Gate Charge

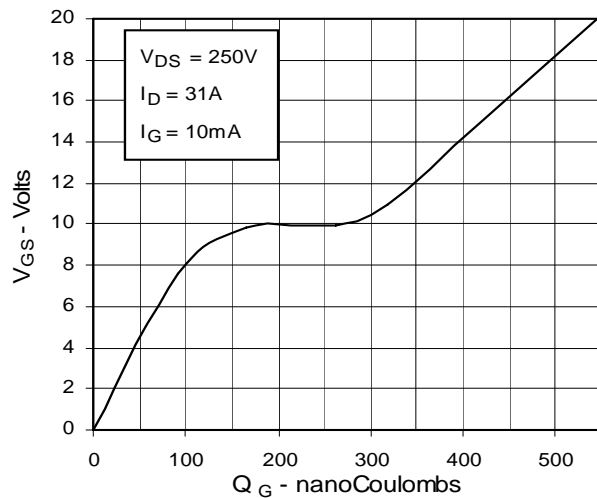


Fig. 11. Capacitance

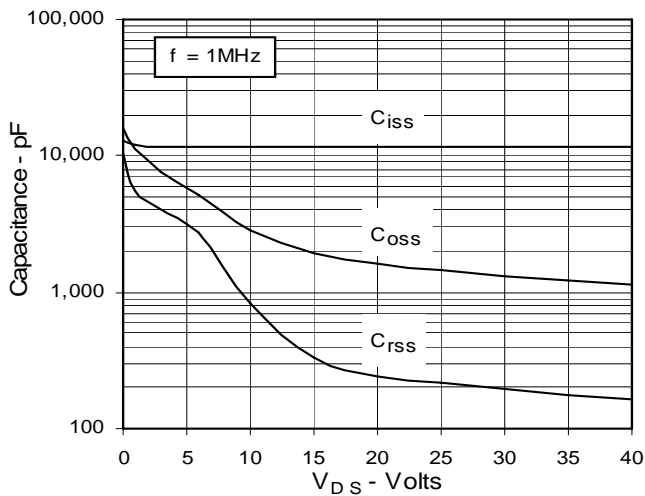


Fig. 12. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

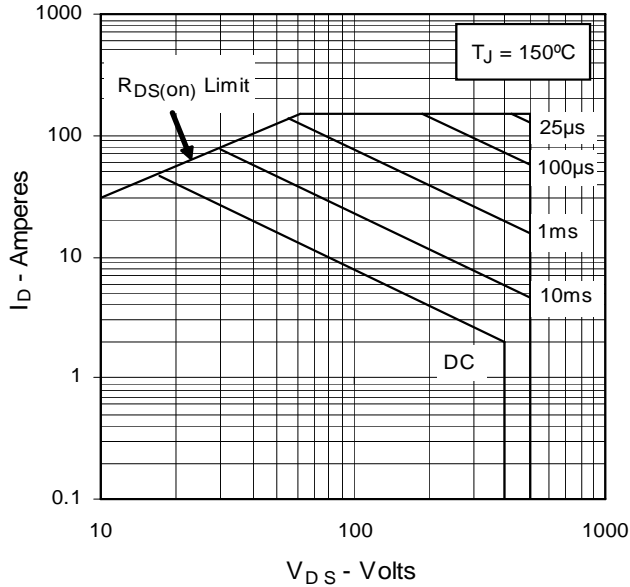


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 90^\circ\text{C}$

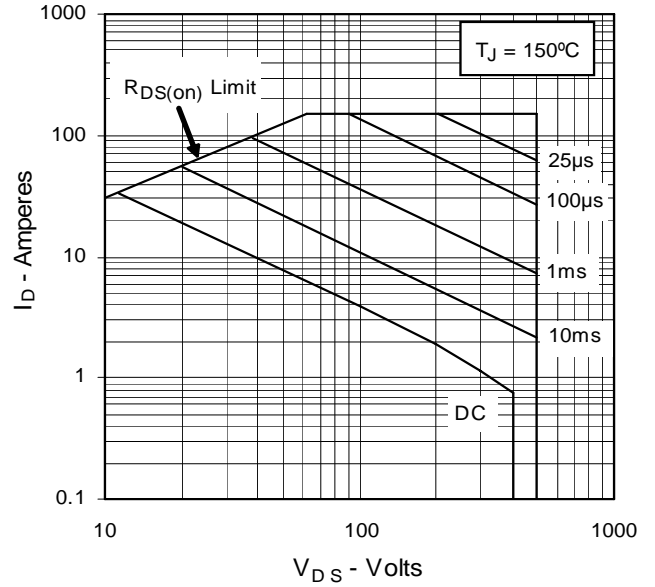


Fig. 14. Maximum Transient Thermal Impedance

